TOSHIBA Photocoupler GaAs IRed & Photo-Triac

# **TLP561J**

Triac Driver
Programmable Controllers
AC-Output Module
Solid State Relay

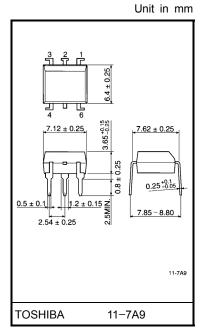
The TOSHIBA TLP561J consists of a zero voltage crossing turn—on photo—triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

- Peak off-state voltage: 600V(min.)
- On-state current: 100mA(max.)
- Isolation voltage: 2500V<sub>rms</sub>(min.)
- UL recognized: UL1577, file no. E67349
- Isolation operating voltage:  $2500V_{ac}$  or  $300V_{dc}$  for isolation Groupe  $C^{*1}$
- Trigger LED current

Classi– Fication*	Trigger LED Current (mA)		Marking Of Classification		
	V <sub>T</sub> =6V, Ta=25°C				
	Min.	Max.			
(IFT7)	_	7	T7		
Standard		10	T7, blank		

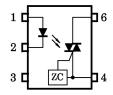
\*Ex. (IFT7); TLP561J(IFT7)

(Note ): Application type name for certification test, please use standard product type name, i.e. TLP561J(IFT7): TLP561J



Weight: 0.39g

### Pin Configuration (top view)



- 1: ANODE
- 2 : CATHODE
- 3: N.C.
- 4:TERMINAL 1
- 6: TERMINAL 2

<sup>\*1:</sup> According to VDE0110, table 4.

## Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
	Forward current	I <sub>F</sub>	50	mA		
	Forward current derating (Ta ≥ 5	ΔI <sub>F</sub> / °C	-0.7	mA / °C		
LED	Peak forward current (100µs pu	lse, 100pps)	I <sub>FP</sub>	1	Α	
	Reverse voltage		VR	5	V	
	Junction temperature	Tj	125	°C		
	Off-state output terminal voltage	$V_{DRM}$	600	V		
	On-state RMS current	Ta = 25°C	l= (= , o)	100	mA	
_		Ta = 70°C	IT(RMS)	50	IIIA	
Detector	On–state current derating (Ta ≥	ΔI <sub>T</sub> / °C	-1.1	mA / °C		
Def	Peak on-state current (100µs p	I <sub>TP</sub>	2	Α		
	Peak nonrepetitive surge curren (Pw = 10ms, DC = 10%)	I <sub>TSM</sub>	1.2	А		
	Junction temperature	Tj	115	°C		
Storage temperature range			T <sub>stg</sub>	-55~125	°C	
Operating temperature range			Topr	-40~100	°C	
Lead soldering temperature (10s)			T <sub>sol</sub>	260	°C	
Isolation voltage (AC, 1min., R.H. ≤ 60%)			BVS	2500	V <sub>rms</sub>	

## **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>AC</sub>	_	_	240	V <sub>ac</sub>
Forward current	IF	15	20	25	mA
Peak on-state current	I <sub>TP</sub>	_	_	_	Α
Operating temperature	T <sub>opr</sub>	-25	_	85	°C

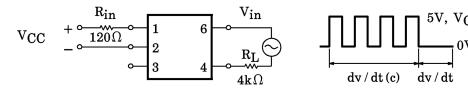
## Individual Electrical Characteristics (Ta = 25°C)

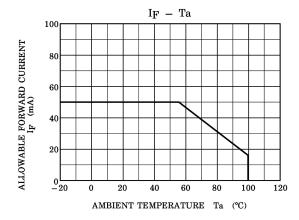
	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10mA	1.0	1.15	1.3	V
	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μΑ
	Capacitance	C <sub>T</sub>	V = 0, f = 1MHz	_	30	_	pF
Detector	Peak off-state current	I <sub>DRM</sub>	V <sub>DRM</sub> = 600V	_	10	1000	nA
	Peak on-state voltage	$V_{TM}$	I <sub>TM</sub> = 100mA	_	1.7	3.0	V
	Holding current	lΗ	_	_	0.6	_	mA
	Critical rate of rise of off–state voltage	dv / dt	V <sub>in</sub> = 240V <sub>rms</sub> , Ta = 85°C (Fig.1	200	500	_	V / µs
	Critical rate of rise of commutating voltage	dv / dt(c)	$V_{in} = 60V_{rms}$ , $I_T = 15mA$ (Fig.1	_	0.2	_	V / µs

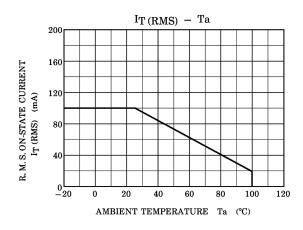
### **Coupled Electrical Characteristics (Ta = 25°C)**

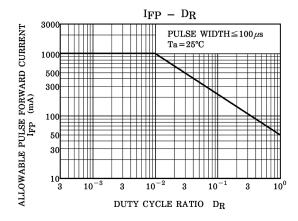
Characteristics	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I <sub>FT</sub>	$V_T = 6V, R_L = 100\Omega$	_	5	10	mA
Inhibit voltage	V <sub>IH</sub>	I <sub>F</sub> = Rated I <sub>FT</sub>	_	_	50	V
Leakage in inhibited state	I <sub>IH</sub>	I <sub>F</sub> = Rated I <sub>FT</sub> V <sub>T</sub> = Rated V <sub>DRM</sub>	_	200	600	μΑ
Capacitance (input to output)	CS	V <sub>S</sub> = 0, f = 1MHz	_	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500V	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
	BVS	AC, 1 minute	2500	_	_	V
Isolation voltage		AC, 1 second, in oil	_	5000	_	V <sub>rms</sub>
		DC, 1 minute, in oil	_	5000	_	V <sub>dc</sub>

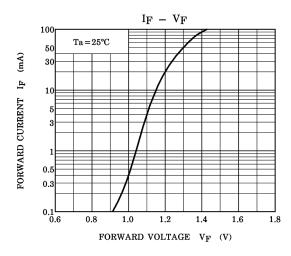
Fig.1: dv / dt test circuit

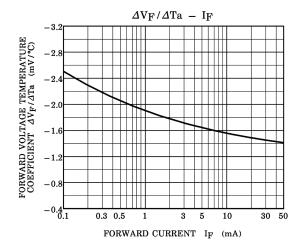


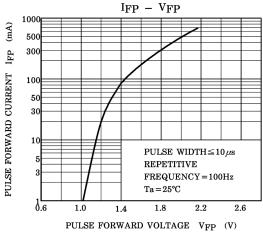




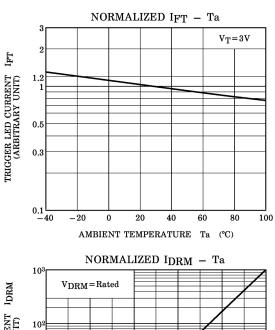


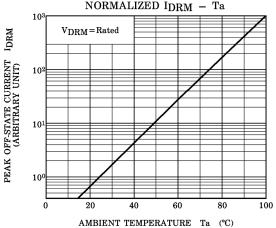


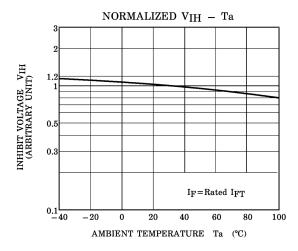


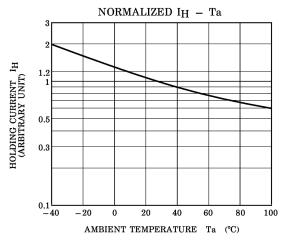


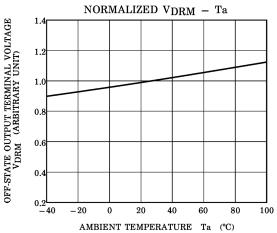
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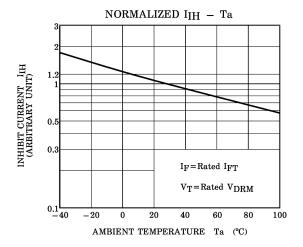












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